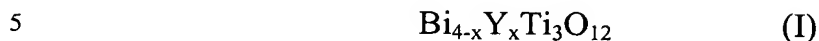


WHAT IS CLAIMED IS :

1. A bismuth yttrium titanate (BYT) thin film having the composition of formula (I):



wherein x is an integer of 0.1 to 2.

2. A process for preparing a bismuth yttrium titanate (BYT) thin film according to claim 1, which comprises bringing the vapors of a Y precursor, a Ti precursor and a Bi precursor into contact with the substrate, together with an oxygen source.
3. The process of claim 2, wherein the Ti precursor is selected from the group consisting of $\text{Ti}(\text{dmae})_4$ (titanium tetradiethylaminoethoxide), $\text{Ti}(\text{dmap})_4$ (titanium tetradiethylaminopropanol), $\text{Ti}(i\text{-OPr})_4$, $\text{Ti}(\text{N}(\text{C}_2\text{H}_5)_2)_4$, $\text{Ti}(\text{N}(\text{CH}_3)_2)_4$ and $\text{Ti}(\text{N}(\text{C}_2\text{H}_5)(\text{CH}_3))_4$.
4. The process of claim 2, wherein the Bi precursor is selected from the group consisting of $\text{Bi}(\text{phenyl})_3$, $\text{Bi}(\text{tmhd})_3$ (tmhd=tetramethylheptadionate), $\text{Bi}(\text{CH}_3)_3$, $\text{Bi}(\text{O}-t\text{-(C}_4\text{H}_9)_3$, $\text{Bi}(\text{C}_7\text{H}_7)_3$, and $\text{Bi}(\text{O}-t\text{-(C}_5\text{H}_{11})_3$.
5. The process of claim 2, wherein the Y precursor is selected from the group consisting of $\text{Y}(\text{tmhd})_3\text{-PMDT}$ (tmhd=tetramethylheptadionate, PMDT=pentamethyldiethylenetriamine), $\text{Y}(\text{tmhd})_3$ and $\text{Y}(\text{N}(\text{Si}(\text{CH}_3)_2)_3)_3$.

6. The process of claim 2, wherein the substrate was heated to a temperature ranging from 250 to 700 °C.

5 7. The process of claim 2, wherein the precursor vapors are generated by dissolving the precursors in an organic solvent and subjecting the solution to a temperature ranging from 200 to 300 °C.

8. The process of claim 2, which further comprises heat-treating the BYT thin film at 500 to 800 °C to impart crystallinity thereto.

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9. An electric or electronic device comprising the BYT thin film according to claim 1.